

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (U-MOS II)

2SK2985

HIGH CURRENT SWITCHING APPLICATIONS

DC-DC CONVERTER, RELAY DRIVE AND MOTOR DRIVE APPLICATIONS

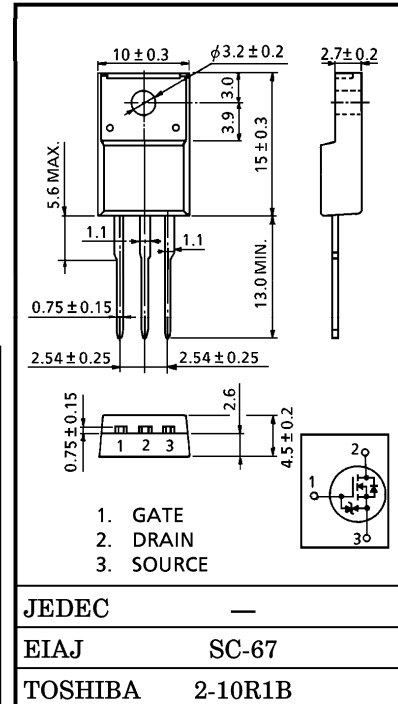
INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 4.5\text{ m}\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 70\text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\text{ }\mu\text{A}$ (Max.) ($V_{DS} = 60\text{ V}$)
- Enhancement-Mode : $V_{th} = 1.3\sim 2.5\text{ V}$ ($V_{DS} = 10\text{ V}$, $I_D = 1\text{ mA}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} = 20\text{ k}\Omega$)	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	45
	Pulse	I_{DP}	180
Drain Power Dissipation ($T_c = 25^\circ\text{C}$)	P_D	45	W
Single Pulse Avalanche Energy**	E_{AS}	701	mJ
Avalanche Current	I_{AR}	45	A
Repetitive Avalanche Energy*	E_{AR}	4.5	mJ
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55\sim 150$	$^\circ\text{C}$



Weight 1.9 g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	2.78	$^\circ\text{C/W}$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	$^\circ\text{C/W}$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 25\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 471\text{ }\mu\text{H}$, $I_{AR} = 45\text{ A}$, $R_G = 25\text{ }\Omega$

**This transistor is an electrostatic sensitive device.
Please handle with caution.**

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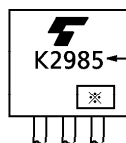
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA	
Drain Cut-off Current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	μA	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	60	—	—	V	
	$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	40	—	—		
Gate Threshold Voltage	V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.3	—	2.5	V	
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$	—	4.5	5.8	m Ω	
		$V_{GS} = 4\text{ V}, I_D = 25\text{ A}$	—	5.8	10		
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 25\text{ A}$	35	70	—	S	
Input Capacitance	C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	9300	—	pF	
Reverse Transfer Capacitance	C_{rss}		—	910	—		
Output Capacitance	C_{oss}		—	1435	—		
Switching Time	Rise Time	t_r		—	18	—	ns
	Turn-on Time	t_{on}		—	50	—	
	Fall Time	t_f		—	110	—	
	Turn-off Time	t_{off}		$V_{IN} : t_r, t_f < 5\text{ ns}$ $Duty \leq 1\%, t_w = 10\ \mu\text{s}$	—	480	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q_g	$V_{DD} \cong 48\text{ V}, V_{GS} = 10\text{ V}, I_D = 45\text{ A}$	—	210	—	nC	
Gate-Source Charge	Q_{gs}		—	145	—		
Gate-Drain ("Miller") Charge	Q_{gd}		—	65	—		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	45	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	180	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.5	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V}$	—	60	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR}/dt = 50\text{ A}/\mu\text{s}$	—	50	—	nC

MARKING

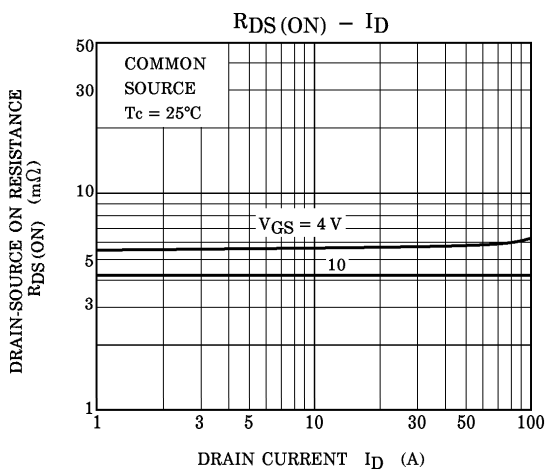
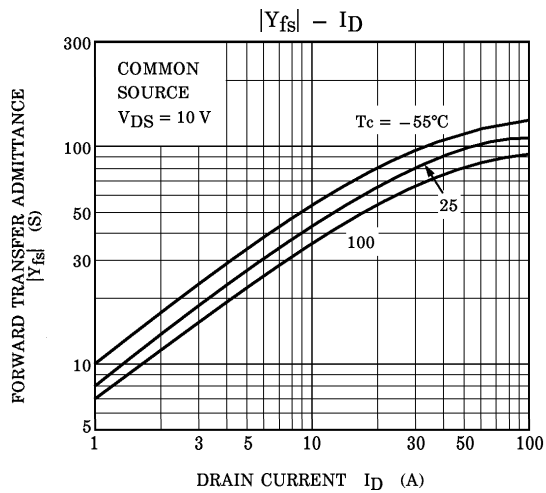
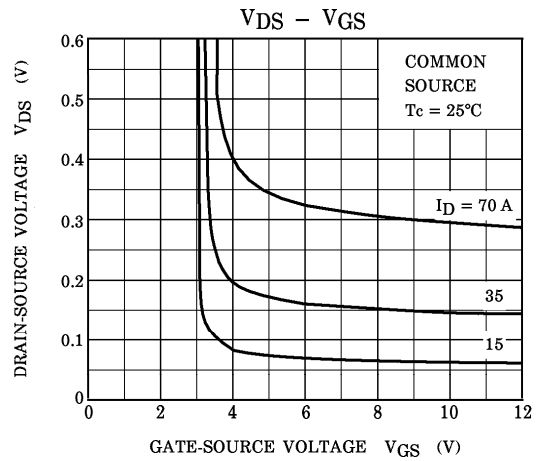
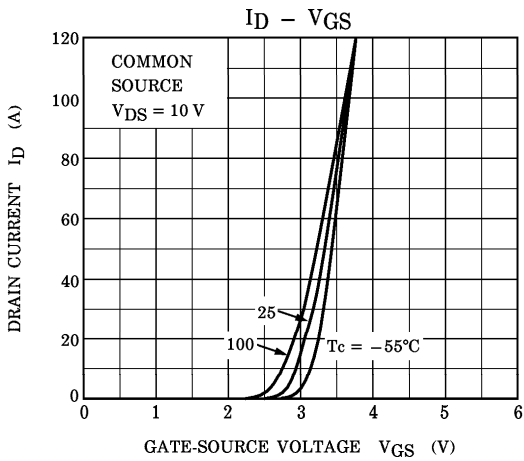
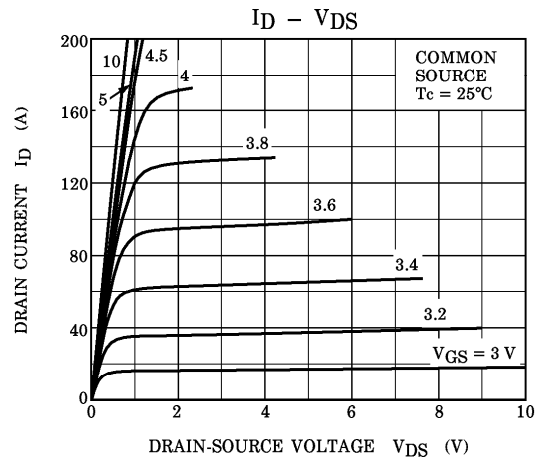
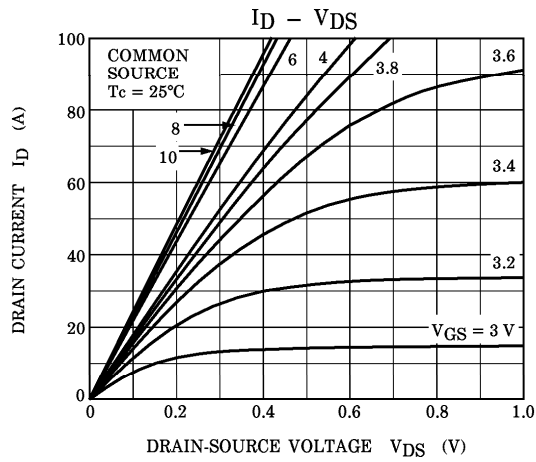


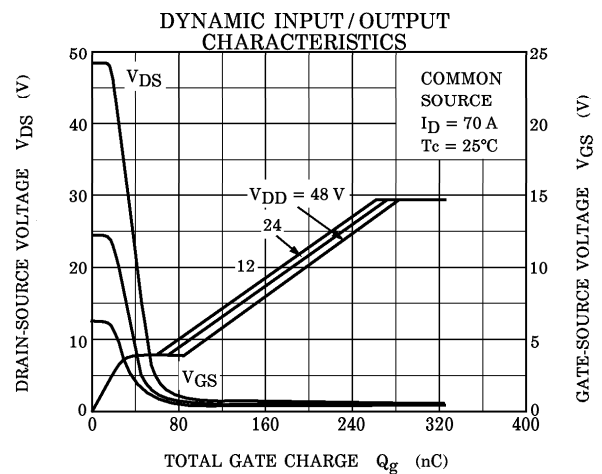
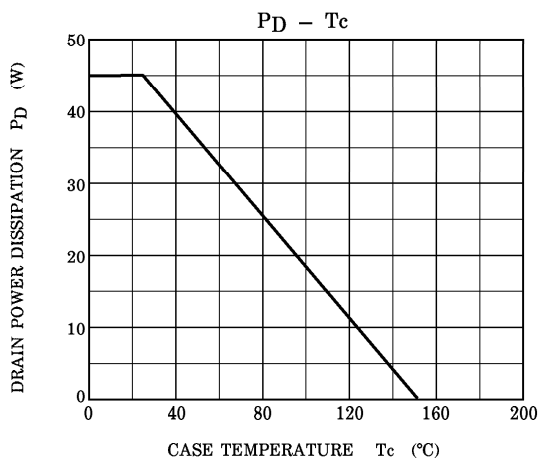
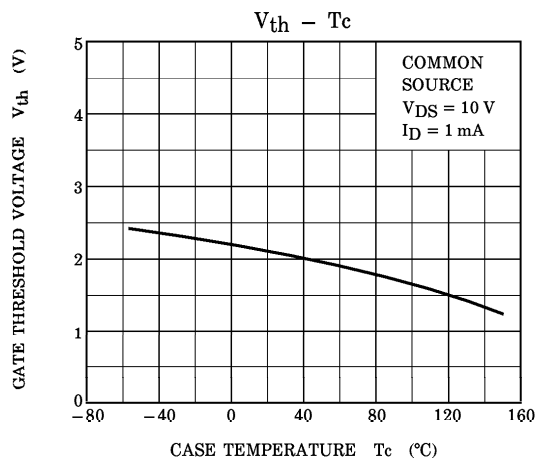
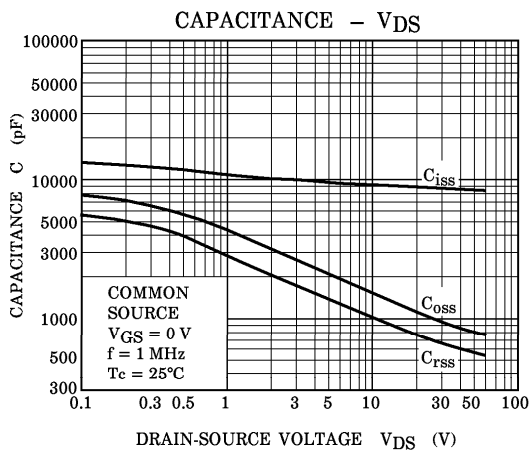
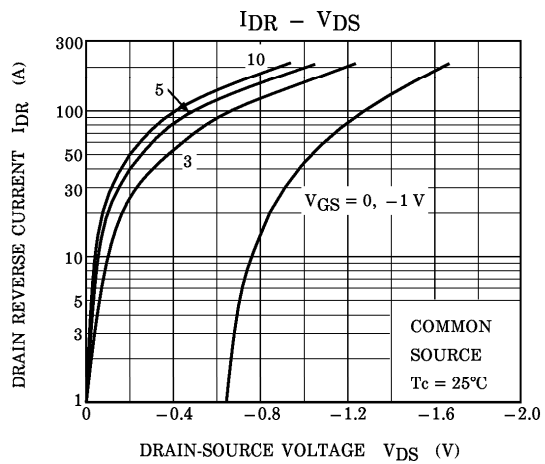
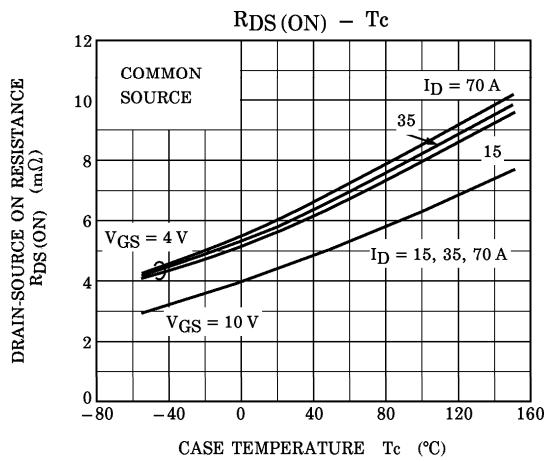
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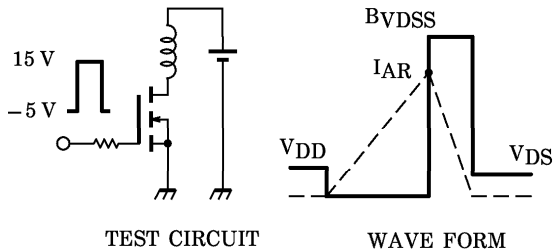
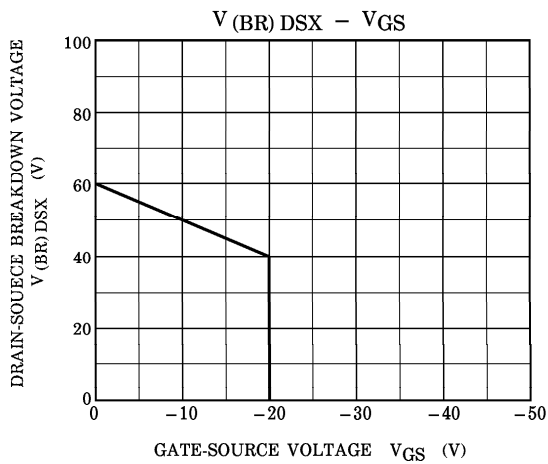
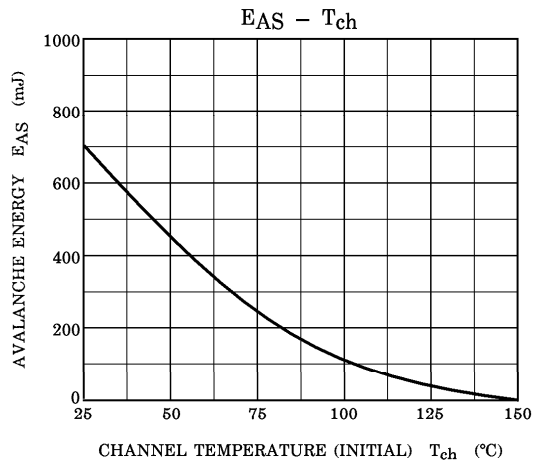
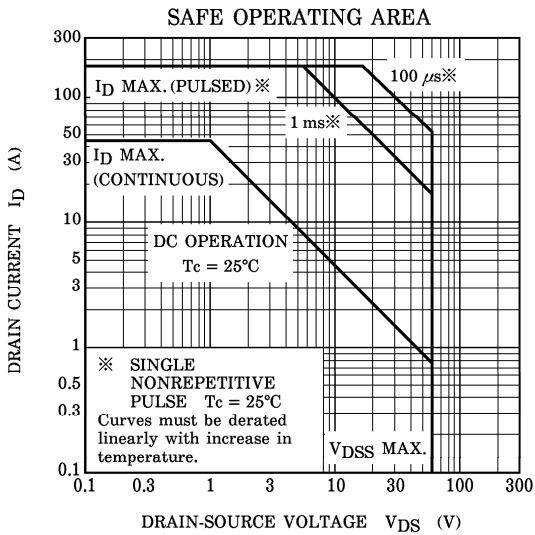
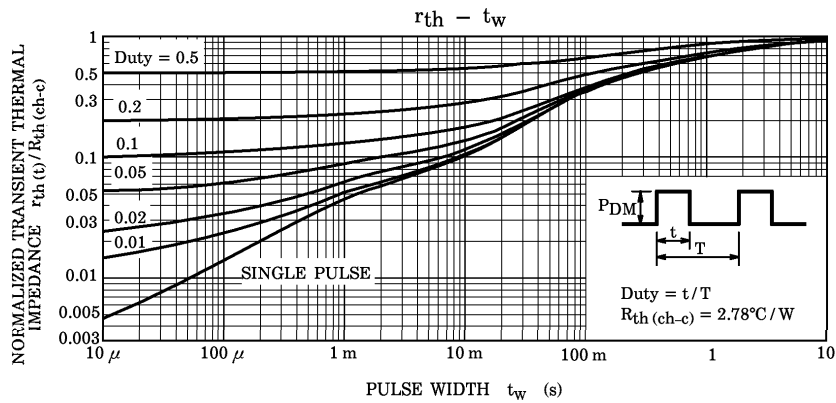
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak $I_{AR} = 45 \text{ A}$, $R_G = 25 \Omega$
 $V_{DD} = 25 \text{ V}$, $L = 471 \mu\text{H}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$